Analog Multiplexers / Demultiplexers

High-Performance Silicon-Gate CMOS

MC74VHC4051, MC74VHC4052, MC74VHC4053

The MC74VHC4051, MC74VHC4052 and MC74VHC4053 utilize silicon–gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF leakage currents. These analog multiplexers/demultiplexers control analog voltages that may vary across the complete power supply range (from V_{CC} to V_{EE}).

The VHC4051, VHC4052 and VHC4053 are identical in pinout to the high-speed HC4051A, HC4052A and HC4053A, and the metal-gate MC14051B, MC14052B and MC14053B. The Channel-Select inputs determine which one of the Analog Inputs/Outputs is to be connected, by means of an analog switch, to the Common Output/Input. When the Enable pin is HIGH, all analog switches are turned off.

The Channel-Select and Enable inputs are compatible with standard CMOS outputs; with pullup resistors they are compatible with LSTTL outputs.

These devices have been designed so that the ON resistance (R_{on}) is more linear over input voltage than R_{on} of metal-gate CMOS analog switches.

- Fast Switching and Propagation Speeds
- Low Crosstalk Between Switches
- Diode Protection on All Inputs/Outputs
- Analog Power Supply Range $(V_{CC} V_{EE}) = 2.0$ to 12.0 V
- Digital (Control) Power Supply Range (V_{CC} GND) = 2.0 to 6.0 V
- Improved Linearity and Lower ON Resistance Than Metal–Gate Counterparts
- Low Noise
- Chip Complexity: VHC4051 184 FETs or 46 Equivalent Gates

VHC4052 — 168 FETs or 42 Equivalent Gates VHC4053 — 156 FETs or 39 Equivalent Gates

VHC4053 — 156 FETs or 39 Equivalent Ga

- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



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MARKING DIAGRAMS

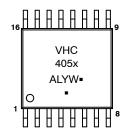


SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F



VHC405x = Specific Device Code

(x = 1, 2 or 3)

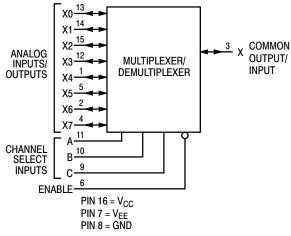
A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or ■ = Pb-Free Package

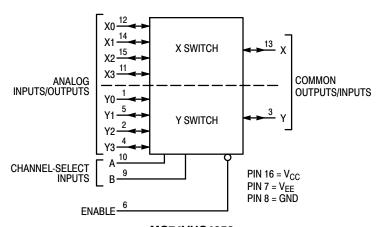
(Note: Microdot may be in either location)

ORDERING INFORMATION

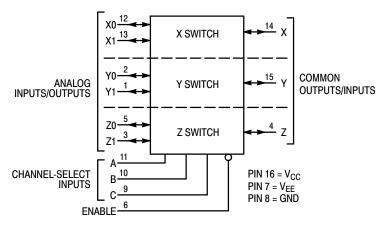
See detailed ordering and shipping information in the package dimensions section on page 16 of this data sheet.



MC74VHC4051
Single-Pole, 8-Position Plus Common Off



MC74VHC4052 Double-Pole, 4-Position Plus Common Off



NOTE: This device allows independent control of each switch. Channel–Select Input A controls the X–Switch, Input B controls the Y–Switch and Input C controls the Z–Switch

MC74VHC4053 Triple Single-Pole, Double-Position Plus Common Off

Figure 1. Logic Diagrams

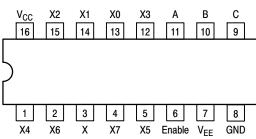


Figure 2. Pinout: MC74VHC4051 (Top View)

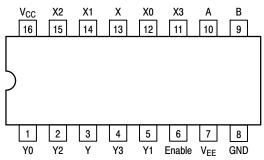


Figure 3. Pinout: MC74VHC4052 (Top View)

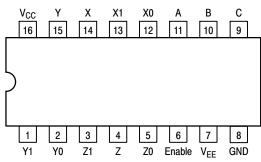


Figure 4. Pinout: MC74VHC4053 (Top View)

FUNCTION TABLE - MC74VHC4051

Conti	Control Inputs			
	- ;	Selec	t	
Enable	С	В	Α	ON Channels
L	L	L	L	X0
L	L	L	Н	X1
L	L	Н	L	X2
L	L	Н	Н	Х3
L	Н	L	L	X4
L	Н	L	Н	X5
L	Н	Н	L	X6
L	Н	Н	Н	X7
н	X	Χ	Χ	NONE

X = Don't Care

FUNCTION TABLE - MC74VHC4052

Contr	ol Input	s			
	Select				
Enable	В	Α	ON Ch	annels	
L	L	L	Y0	X0	
L	L	Н	Y1	X1	
L	Н	L	Y2	X2	
L	Н	Н	Y3	ХЗ	
Н	X	Χ	NONE		

X = Don't Care

FUNCTION TABLE - MC74VHC4053

Contr	Control Inputs					
Enable	Select Enable C B A			10	N Chann	els
L	L	L	L	Z0	Y0	X0
L	L	L	Н	Z0	Y0	X1
L	L	Н	L	Z0	Y1	X0
L	L	Н	Н	Z0	Y1	X1
L	Н	L	L	Z1	Y0	X0
L	Н	L	Н	Z1	Y0	X1
L	Н	Н	L	Z1	Y1	X0
L	Н	Н	Н	Z1	Y1	X1
Н	Х	Χ	Χ		NONE	

X = Don't Care

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage (Referenced to GND) (Referenced to V _{EE})	- 0.5 to + 7.0 - 0.5 to + 14.0	٧
V _{EE}	Negative DC Supply Voltage (Referenced to GND)	- 7.0 to + 5.0	V
V _{IS}	Analog Input Voltage	V _{EE} - 0.5 to V _{CC} + 0.5	٧
V _{in}	Digital Input Voltage (Referenced to GND)	-0.5 to V_{CC} + 0.5	٧
I	DC Current, Into or Out of Any Pin	± 25	mA
P _D	Power Dissipation in Still Air SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature Range	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or $V_{\rm CC}$). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating — SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage (Referenced to GND) (Referenced to V _{EE})	2.0 2.0	6.0 12.0	V
V _{EE}	Negative DC Supply Voltage, Output (Referenced to GND)	- 6.0	GND	V
V _{IS}	Analog Input Voltage	V _{EE}	V _{CC}	٧
V _{in}	Digital Input Voltage (Referenced to GND)	GND	V _{CC}	V
V _{IO} *	Static or Dynamic Voltage Across Switch		1.2	V
T _A	Operating Temperature Range, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise/Fall Time $V_{CC} = 2.0 \text{ V}$ (Channel Select or Enable Inputs) $V_{CC} = 3.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0 0	1000 800 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

^{*}For voltage drops across switch greater than 1.2V (switch on), excessive V_{CC} current may be drawn; i.e., the current out of the switch may contain both V_{CC} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

DC CHARACTERISTICS — Digital Section (Voltages Referenced to GND) V_{EE} = GND, Except Where Noted

				v _{cc}	Guara	nteed Lim	nit	
Symbol	Parameter	Conditio	n	V	-55 to 25°C	≤ 85°C	≤125°C	Unit
V _{IH}	Minimum High-Level Input Voltage, Channel-Select or Enable Inputs	R _{on} = Per Spec		2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	V
V _{IL}	Maximum Low-Level Input Voltage, Channel-Select or Enable Inputs	R _{on} = Per Spec		2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
l _{in}	Maximum Input Leakage Current, Channel-Select or Enable Inputs	$V_{in} = V_{CC}$ or GND, $V_{EE} = -6.0 \text{ V}$		6.0	± 0.1	± 1.0	± 1.0	μА
I _{CC}	Maximum Quiescent Supply Current (per Package)	Channel Select, Enal $V_{IS} = V_{CC}$ or GND; $V_{IO} = 0 \text{ V}$		6.0 6.0	1 4	10 40	40 80	μΑ

DC ELECTRICAL CHARACTERISTICS Analog Section

					Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC} V	V _{EE} V	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
R _{on}	Maximum "ON" Resistance	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = V_{CC} \text{ to } V_{EE}$ $I_{S} \leq 2.0 \text{ mA}$ (Figures 5 through 11)	3.0 4.5 4.5 6.0	0.0 0.0 - 4.5 - 6.0	200 160 120 100	240 200 150 125	320 280 170 140	Ω
		$\begin{split} &V_{in} = V_{IL} \text{ or } V_{IH} \\ &V_{IS} = V_{CC} \text{ or } V_{EE} \text{ (Endpoints)} \\ &I_{S} \leq 2.0 \text{ mA} \\ &\text{(Figures 5 through11)} \end{split}$	3.0 4.5 4.5 6.0	0.0 0.0 - 4.5 - 6.0	150 110 90 80	180 140 120 100	230 190 140 115	
ΔR_{on}	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$\begin{split} &V_{in} = V_{IL} \text{ or } V_{IH} \\ &V_{IS} = 1/2 (V_{CC} - V_{EE}) \\ &I_{S} \leq 2.0 \text{ mA} \end{split}$	3.0 4.5 4.5 6.0	0.0 0.0 - 4.5 - 6.0	40 20 10 10	50 25 15 12	80 40 18 14	Ω
I _{off}	Maximum Off-Channel Leakage Current, Any One Channel	$V_{in} = V_{IL} \text{ or } V_{IH};$ $V_{IO} = V_{CC} - V_{EE};$ Switch Off (Figure 12)	6.0	- 6.0	0.1	0.5	1.0	μА
	Maximum Off-Channel VHC4051 Leakage Current, VHC4052 Common Channel VHC4053	10 00 LL	6.0 6.0 6.0	- 6.0 - 6.0 - 6.0	0.2 0.1 0.1	2.0 1.0 1.0	4.0 2.0 2.0	
I _{on}	Maximum On-Channel VHC4051 Leakage Current, VHC4052 Channel-to-Channel VHC4053		6.0 6.0 6.0	- 6.0 - 6.0 - 6.0	0.2 0.1 0.1	2.0 1.0 1.0	4.0 2.0 2.0	μΑ

AC CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

		V	v _{cc}	Gua	aranteed Lim	nit	
Symbol	Parameter		V	-55 to 25°C	≤ 85 °C	≤125°C	Unit
t _{PLH} ,	Maximum Propagation Delay, Channel-Select to Analog (Output 2	2.0	270	320	350	ns
t_PHL	(Figures 18, 19)	3	3.0	90	110	125	
		4	4.5	59	79	85	
		6	6.0	45	65	75	
t _{PLH} ,	Maximum Propagation Delay, Analog Input to Analog Out	put 2	2.0	40	60	70	ns
t_PHL	(Figures 20, 21)	3	3.0	25	30	32	
		4	4.5	12	15	18	
		6	6.0	10	13	15	
t _{PLZ} ,	Maximum Propagation Delay, Enable to Analog Output	2	2.0	160	200	220	ns
t_PHZ	(Figures 22, 23)	3	3.0	70	95	110	
		4	4.5	48	63	76	
		(6.0	39	55	63	
t_{PZL} ,	Maximum Propagation Delay, Enable to Analog Output	2	2.0	245	315	345	ns
t_{PZH}	(Figures 22, 23)	3	3.0	115	145	155	
			4.5	49	69	83	
		6	6.0	39	58	67	
C _{in}	Maximum Input Capacitance, Channel-Select or Enable I	nputs		10	10	10	pF
C _{I/O}	Maximum Capacitance Ana	log I/O		35	35	35	pF
	(All Switches Off) Common O/I: VH	C4051		130	130	130	
	VH	C4052		80	80	80	
	VH	C4053		50	50	50	
ı	Feedth	hrough		1.0	1.0	1.0	

			Typical @ 25°C, V _{CC} = 5.0 V, V _{EE} = 0 V	
C_{PD}	Power Dissipation Capacitance (Figure 25)*	VHC4051	45	pF
		VHC4052	80	
		VHC4053	45	

^{*}Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

ADDITIONAL APPLICATION CHARACTERISTICS (GND = 0 V)

			V _{CC}	V _{EE}	Limit* 25°C			
Symbol	Parameter	Condition	v	V				Unit
BW	Maximum On–Channel Bandwidth or Minimum Frequency Response (Figure 15)	$\begin{split} f_{in} &= \text{1MHz Sine Wave; Adjust } f_{in} \text{ Voltage to} \\ \text{Obtain 0dBm at V}_{OS}; \text{Increase } f_{in} \\ \text{Frequency Until dB Meter Reads } &-3\text{dB;} \\ R_L &= 50\Omega, C_L = 10\text{pF} \end{split}$	2.25 4.50 6.00	-2.25 -4.50 -6.00	'51 80 80 80	'52 95 95 95	'53 120 120 120	MHz
_	Off-Channel Feedthrough Isolation (Figure 16)	f_{in} = Sine Wave; Adjust f_{in} Voltage to Obtain 0dBm at V_{IS} f_{in} = 10kHz, R_L = 600 Ω , C_L = 50pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		-50 -50 -50		dB
		f_{in} = 1.0MHz, R_L = 50 Ω , C_L = 10pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		-40 -40 -40		
_	Feedthrough Noise. Channel–Select Input to Common I/O (Figure 17)	$\begin{split} &V_{in} \leq \text{1MHz Square Wave } (t_r = t_f = 6\text{ns}); \\ &\text{Adjust R}_L \text{ at Setup so that } I_S = 0\text{A}; \\ &\text{Enable} = \text{GND} & \text{R}_L = 600\Omega, \ C_L = 50\text{pF} \end{split}$	2.25 4.50 6.00	-2.25 -4.50 -6.00		25 105 135		mV _{PP}
		R_L = 10kΩ, C_L = 10pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		35 145 190		
_	Crosstalk Between Any Two Switches (Figure 24) (Test does not apply to VHC4051)	$\begin{aligned} f_{in} &= \text{Sine Wave; Adjust } f_{in} \text{ Voltage to} \\ &\text{Obtain 0dBm at V}_{IS} \\ &f_{in} &= \text{10kHz, R}_{L} = 600\Omega, C_{L} = \text{50pF} \end{aligned}$	2.25 4.50 6.00	-2.25 -4.50 -6.00		-50 -50 -50		dB
		f_{in} = 1.0MHz, R_L = 50 Ω , C_L = 10pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		-60 -60 -60		
THD	Total Harmonic Distortion (Figure 26)	$\begin{split} f_{in} &= 1 \text{kHz}, R_L = 10 \text{k}\Omega, C_L = 50 \text{pF} \\ \text{THD} &= \text{THD}_{measured} - \text{THD}_{source} \\ V_{IS} &= 4.0 \text{V}_{PP} \text{sine wave} \\ V_{IS} &= 8.0 \text{V}_{PP} \text{sine wave} \\ V_{IS} &= 11.0 \text{V}_{PP} \text{sine wave} \end{split}$	2.25 4.50 6.00	-2.25 -4.50 -6.00		0.10 0.08 0.05		%

^{*}Limits not tested. Determined by design and verified by qualification.

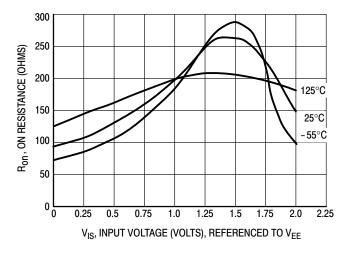


Figure 5. Typical On Resistance, V_{CC} – V_{EE} = 2.0 V

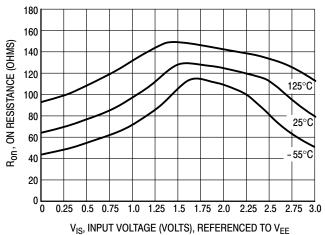


Figure 6. Typical On Resistance, V_{CC} – V_{EE} = 3.0 V

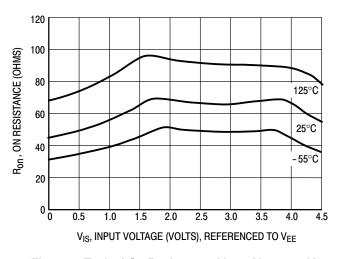


Figure 7. Typical On Resistance, V_{CC} – V_{EE} = 4.5 V

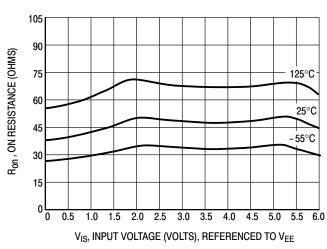


Figure 8. Typical On Resistance, $V_{CC} - V_{EE} = 6.0 \text{ V}$

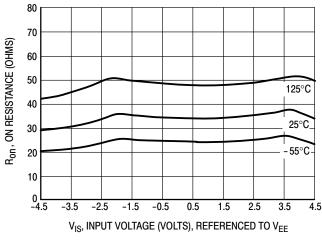


Figure 9. Typical On Resistance, $V_{CC} - V_{EE} = 9.0 \text{ V}$

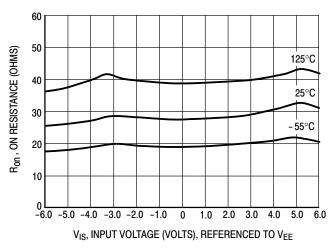


Figure 10. Typical On Resistance, $V_{CC} - V_{EE} = 12.0 \text{ V}$

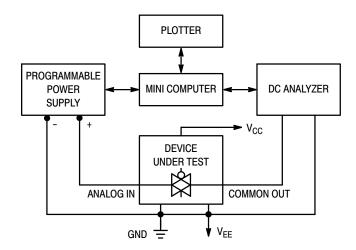


Figure 11. On Resistance Test Set-Up

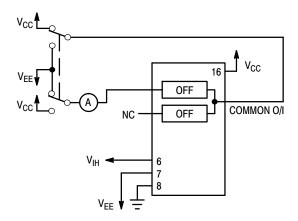


Figure 12. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

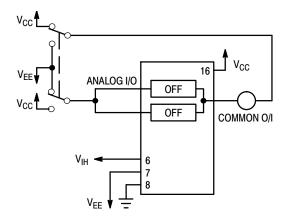


Figure 13. Maximum Off Channel Leakage Current, Common Channel, Test Set-Up

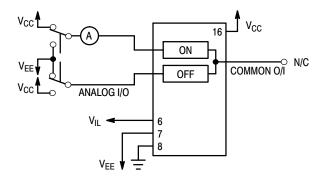


Figure 14. Maximum On Channel Leakage Current, Channel to Channel, Test Set-Up

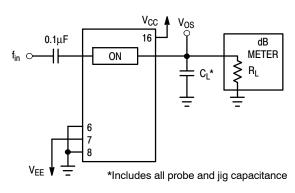


Figure 15. Maximum On Channel Bandwidth, Test Set-Up

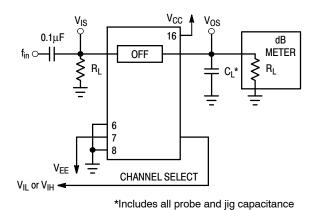
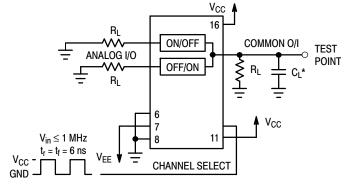
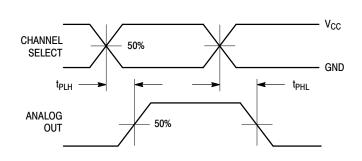


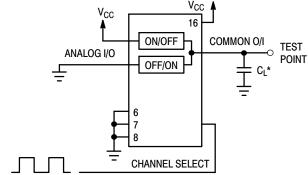
Figure 16. Off Channel Feedthrough Isolation, Test Set-Up



*Includes all probe and jig capacitance

Figure 17. Feedthrough Noise, Channel Select to Common Out, Test Set-Up

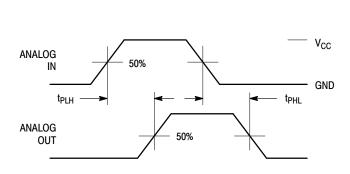


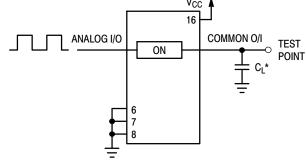


*Includes all probe and jig capacitance

Figure 18. Propagation Delays, Channel Select to Analog Out

Figure 19. Propagation Delay, Test Set-Up Channel Select to Analog Out





*Includes all probe and jig capacitance

Figure 20. Propagation Delays, Analog In to Analog Out

Figure 21. Propagation Delay, Test Set-Up
Analog In to Analog Out

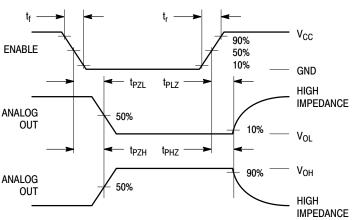


Figure 22. Propagation Delays, Enable to Analog Out

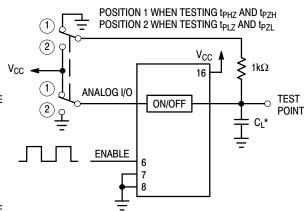
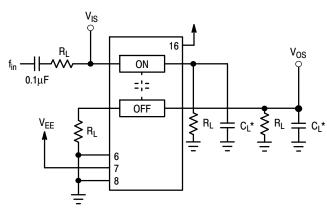


Figure 23. Propagation Delay, Test Set-Up Enable to Analog Out



*Includes all probe and jig capacitance

Figure 24. Crosstalk Between Any Two Switches, Test Set-Up

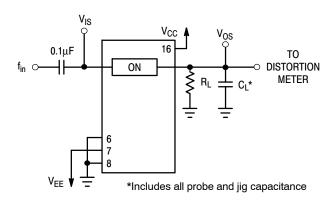


Figure 26. Total Harmonic Distortion, Test Set-Up

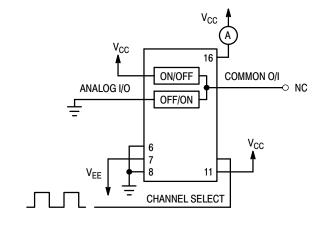


Figure 25. Power Dissipation Capacitance, Test Set-Up

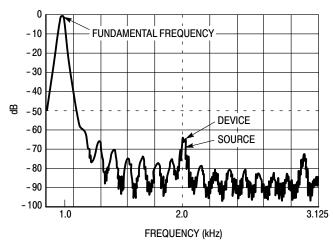


Figure 27. Plot, Harmonic Distortion

APPLICATIONS INFORMATION

The Channel Select and Enable control pins should be at V_{CC} or GND logic levels. V_{CC} being recognized as a logic high and GND being recognized as a logic low. In this example:

$$V_{CC}$$
 = +5V = logic high
GND = 0V = logic low

The maximum analog voltage swings are determined by the supply voltages V_{CC} and V_{EE} . The positive peak analog voltage should not exceed V_{CC} . Similarly, the negative peak analog voltage should not go below V_{EE} . In this example, the difference between V_{CC} and V_{EE} is ten volts. Therefore, using the configuration of Figure 28, a maximum analog signal of ten volts peak—to—peak can be controlled. Unused analog inputs/outputs may be left floating (i.e., not connected). However, tying unused analog inputs and

outputs to V_{CC} or GND through a low value resistor helps minimize crosstalk and feedthrough noise that may be picked up by an unused switch.

Although used here, balanced supplies are not a requirement. The only constraints on the power supplies are that:

$$\begin{split} V_{CC} - GND &= 2 \text{ to 6 volts} \\ V_{EE} - GND &= 0 \text{ to -6 volts} \\ V_{CC} - V_{EE} &= 2 \text{ to 12 volts} \\ and V_{EE} &\leq GND \end{split}$$

When voltage transients above V_{CC} and/or below V_{EE} are anticipated on the analog channels, external Germanium or Schottky diodes (D_x) are recommended as shown in Figure 29. These diodes should be able to absorb the maximum anticipated current surges during clipping.

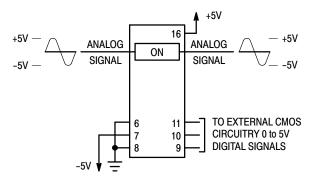


Figure 28. Application Example

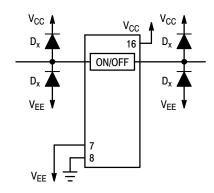
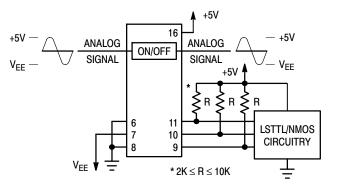
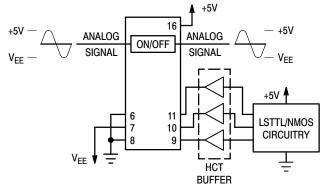


Figure 29. External Germanium or Schottky Clipping Diodes



a. Using Pull-Up Resistors



b. Using HCT Interface

Figure 30. Interfacing LSTTL/NMOS to CMOS Inputs

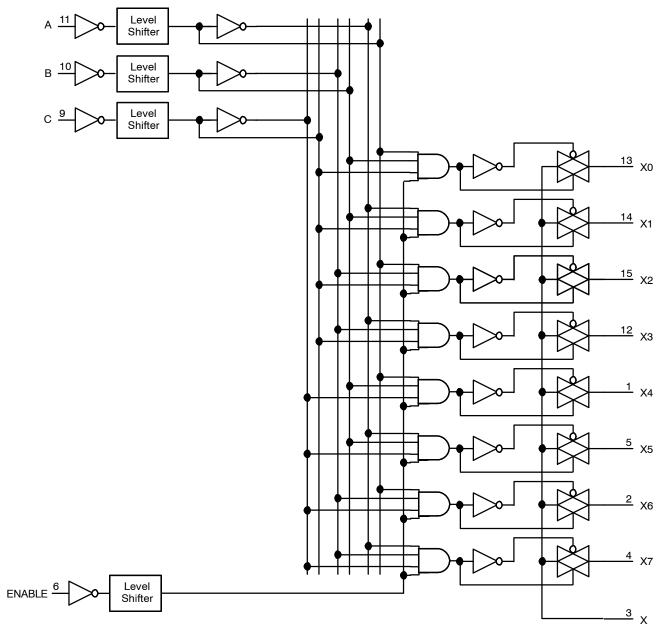
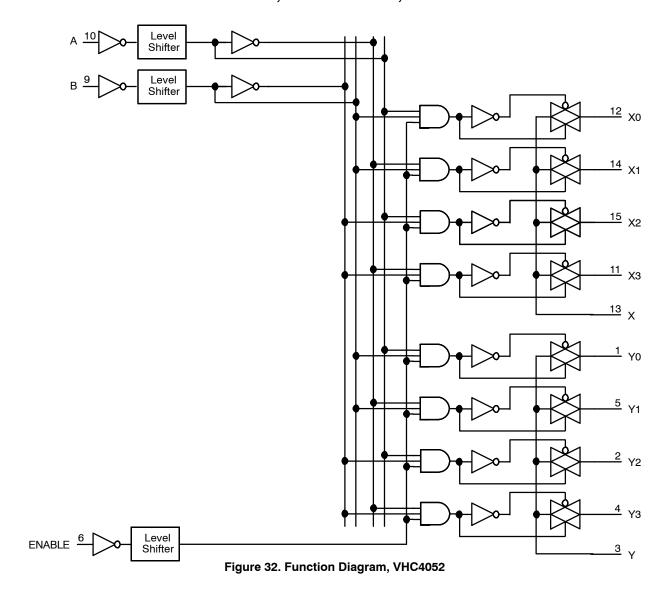


Figure 31. Function Diagram, VHC4051



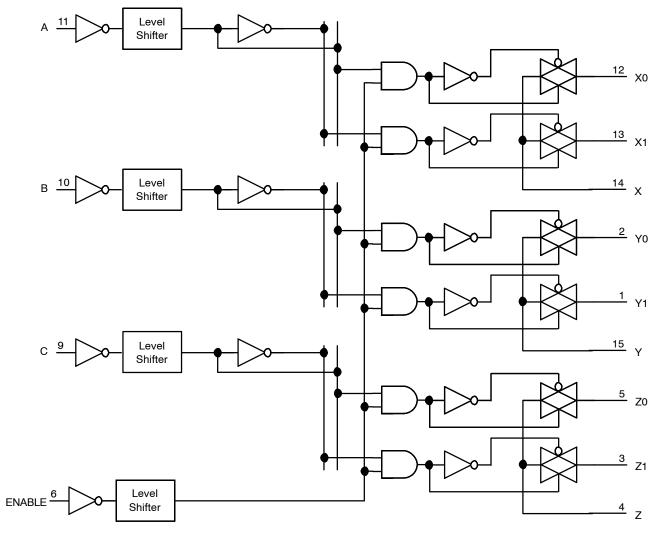


Figure 33. Function Diagram, VHC4053

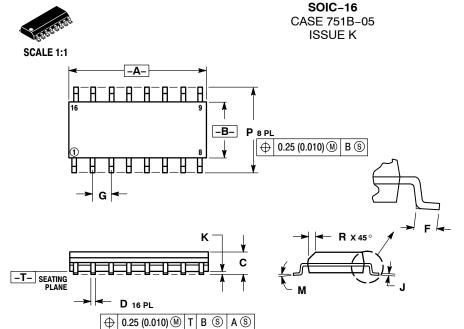
ORDERING & SHIPPING INFORMATION

Device	Package	Shipping [†]
MC74VHC4051DR2G		
MC74VHC4052DR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel
MC74VHC4053DR2G] , , ,	
MC74VHC4051DTR2G		
NLVVHC4051DTR2G*]	
MC74VHC4052DTR2G	TSSOP-16	OFOO / Tong % Dool
NLVVHC4052DTR2G*	(Pb-Free)	2500 / Tape & Reel
MC74VHC4053DTR2G		
NLVVHC4053DTR2G*		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP

Capable.

MECHANICAL CASE OUTLINE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER AND STATEMENT OF THE NATIONAL STATEMENT
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010 0.01	

2. 3.	COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE COLLECTOR COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE	2. 3. 4. 5. 6. 7. 8. 9. 10.	CATHODE ANODE	2. 3. 4. 5. 6. 7. 8. 9. 10.	COLLECTOR, DYE #1 BASE, #1 EMITTER, #1 COLLECTOR, #1 COLLECTOR, #2 BASE, #2 EMITTER, #2 COLLECTOR, #2 COLLECTOR, #2 COLLECTOR, #3	STYLE 4: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	COLLECTOR, DYN COLLECTOR, #1 COLLECTOR, #2 COLLECTOR, #3 COLLECTOR, #3 COLLECTOR, #4 COLLECTOR, #4 BASE, #4 EMITTER, #4 BASE, #3 EMITTER, #3 BASE, #2		
14.	COLLECTOR		NO CONNECTION	14.		14.		SOLDERING	FOOTPRINT
15.	EMITTER		ANODE	15.		15.	BASE, #1	8	X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1		^ 40
					,		,		6X 1.12
STYLE 5:	DDAIN DVE #4	STYLE 6:	OATHODE	STYLE 7:	COURCE N OU			'	0.1.12
PIN 1.	DRAIN, DYE #1	PIN 1.		PIN 1.	SOURCE N-CH	Τ\		<u></u>	16
2.	DRAIN, #1	2. 3.	CATHODE CATHODE	2.	COMMON DRAIN (OUTPU			↓ └──	10
3. 4.	DRAIN, #2 DRAIN, #2	3. 4.	CATHODE	3. 4.	COMMON DRAIN (OUTPU' GATE P-CH	1)		<u>*</u>	
4. 5.	DRAIN, #2 DRAIN, #3	4. 5.	CATHODE	4. 5.	COMMON DRAIN (OUTPU	Τ\			
5. 6.	DRAIN, #3	5. 6.	CATHODE	6.	COMMON DRAIN (OUTPU		1	.58 ∱	
7.	DRAIN, #4	7.		7.	COMMON DRAIN (OUTPU		U.	.58	
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	.,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU	T)			
11.	,	11.		11.	COMMON DRAIN (OUTPU				
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPU	T)			
13.	GATE, #2	13.	ANODE	13.	GATE N-CH				
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPU	T)			—— ↓ PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPU	T)			<u>+-+</u> -
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH				
								8	9 ++ 7
								,	DIMENSIONS: MILLIMETERS

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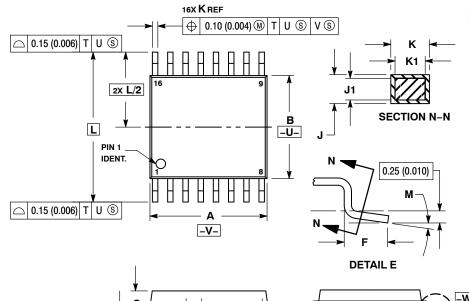
D

-T- SEATING PLANE



TSSOP-16 CASE 948F-01 ISSUE B

DATE 19 OCT 2006



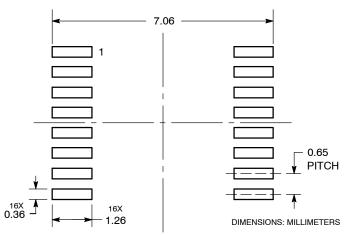
NOTES

- JIES:
 DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD
 FLASH. PROTRUSIONS OR GATE BURRS.
 MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
C		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026 BSC		
Н	0.18	0.28	0.007	0.011	
7	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
М	٥°	QΟ	٥°	gο	



G



GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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